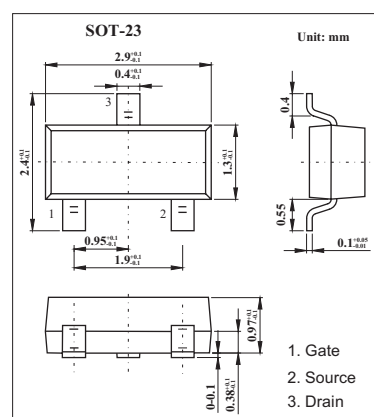
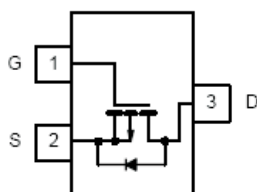


P-Channel 12-V (D-S) MOSFET

KI2335DS

■ Features

●

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	5 sec	Steady State	Unit
Drain-Source Voltage	V_{DS}	-12		V
Gate-Source Voltage	V_{GS}	± 8		V
Continuous Drain Current ($T_J=150^\circ\text{C}$) *1,2 $T_A=25^\circ\text{C}$ $T_A=70^\circ\text{C}$	I_D	-4.0 -3.3	-3.2 -2.6	A
Pulsed Drain Current	I_{DM}	-15		A
Continuous Source Current (Diode Conduction)*1,2	I_S	-1.6		A
Power Dissipation *1,2 $T_A=25^\circ\text{C}$ $T_A=70^\circ\text{C}$	P_D	1.25 0.8	0.75 0.48	W
Junction Temperature	T_J	150		$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150		$^\circ\text{C}$

*1 Surface Mounted on 1" X 1" FR4 Board.

*2 Pulse width limited by maximum junction temperature.

■ Thermal Resistance Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient * $t \leq 5 \text{ sec}$	R_{thJA}	75	100	$^\circ\text{C/W}$
Maximum Junction-to-Ambient Steady State		120	166	
Maximum Junction-to-Foot (Drain) Steady State	R_{thJF}	40	50	

* Surface Mounted on 1" X 1" FR4 Board.

KI2335DS

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$, $I_D = -10\text{ }\mu\text{ A}$	-12			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{ A}$	-0.45			
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -9.6\text{ V}$, $V_{GS} = 0\text{ V}$			-1	$\mu\text{ A}$
		$V_{DS} = -9.6\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^\circ\text{C}$			-10	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}$, $V_{GS} = -4.5\text{ V}$	-15			A
		$V_{DS} \leq -5\text{ V}$, $V_{GS} = -2.5\text{ V}$	-6			
Drain-Source On-State Resistance *	$r_{DS(on)}$	$V_{GS} = -4.5\text{ V}$, $I_D = -4.0\text{ A}$		0.042	0.051	Ω
		$V_{GS} = -2.5\text{ V}$, $I_D = -3.5\text{ A}$		0.058	0.070	
		$V_{GS} = -1.8\text{ V}$, $I_D = -2.0\text{ A}$		0.082	0.106	
Forward Transconductance *	g_{fs}	$V_{DS} = -5\text{ V}$, $I_D = -4.0\text{ A}$		7		S
Diode Forward Voltage *	V_{SD}	$I_S = -1.6\text{ A}$, $V_{GS} = 0\text{ V}$			-1.2	V
Total Gate Charge	Q_g	$V_{DS} = -6\text{ V}$, $V_{GS} = -4.5\text{ V}$, $I_D = -4.0\text{ A}$		9	15	nC
Gate-Source Charge	Q_{gs}			1.9		
Gate-Drain Charge	Q_{gd}			1.5		
Input Capacitance	C_{iss}	$V_{DS} = -6\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$		1225		pF
Output Capacitance	C_{oss}			260		
Reverse Transfer Capacitance	C_{rss}			130		
Turn-On Time	$t_{d(on)}$	$V_{DD} = -6\text{ V}$, $R_L = 6\text{ }\Omega$, $I_D = -1.0\text{ A}$, $V_{GEN} = -4.5\text{ V}$, $R_G = 6\text{ }\Omega$		13	20	ns
	t_r			15	25	
Turn-Off Time	$t_{d(off)}$			50	70	
	t_f			19	35	

* Pulse test: $PW \leq 300\text{ }\mu\text{s}$ duty cycle $\leq 2\%$.

■ Marking

Marking	E5
---------	----